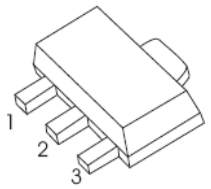
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-89-3L Plastic-Encapsulate Transistors

SOT-89-3L



1. BASE
2. COLLECTOR
3. EMITTER

2SC4548 TRANSISTOR (NPN)

FEATURES

- Small Flat Package
- High Breakdown Voltage
- Excellent h_{FE} Linearity

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	400	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	200	mA
P_C	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	250	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=10μA,I_E=0	400			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA,I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=300V,I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=4V,I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}=10V, I_C=50mA	60		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=50mA,I_B=5mA			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=50mA,I_B=5mA			1	V
Transition frequency	f_T	V_{CE}=30V,I_C=10mA		70		MHz
Collector output capacitance	C_{ob}	V_{CB}=30V, I_E=0, f=1MHz		4		pF

CLASSIFICATION OF h_{FE}

RANK	D	E
RANGE	60－120	100－200
MARKING	CN	